Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.8)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	25	mA
				30	
I_H	I_T =500mA		MAX.	15	mA
dV/dt	V_D=670V Gate Open T_j =125		MIN.	200	V/μs
(dI/dt)c	(dV/dt)c=10V/μs T_j=125		MIN.	3	A/ms
t_{on}	I_G=20mA I_A=200mA I_R=20mA T_j=25		TYP.	2.5	μs

ORDERING INFORMATION

J ST 12 E -1000 SW -/

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Triacs

SW:I_{GT1-3} 10mA

1000:V_{DRM} /V_{RRM} 1000V

FIG.1: Maximum power dissipation versus RMS on-state current

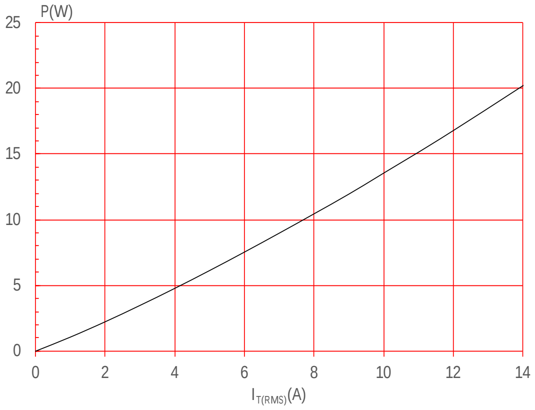


FIG.2: RMS on-state current versus case temperature

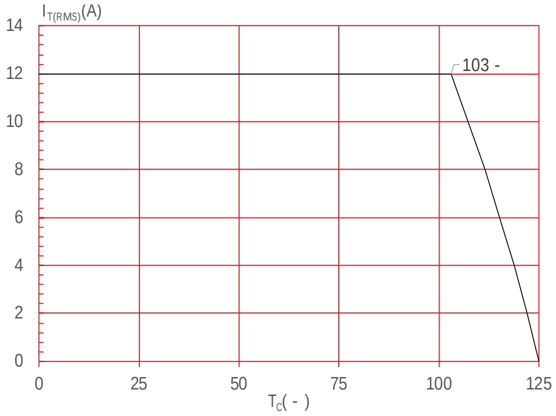


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35μm)(full cycle)

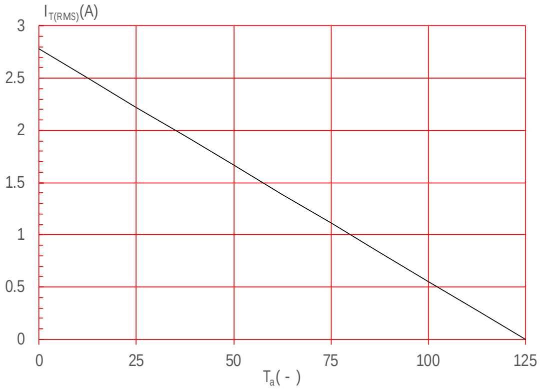
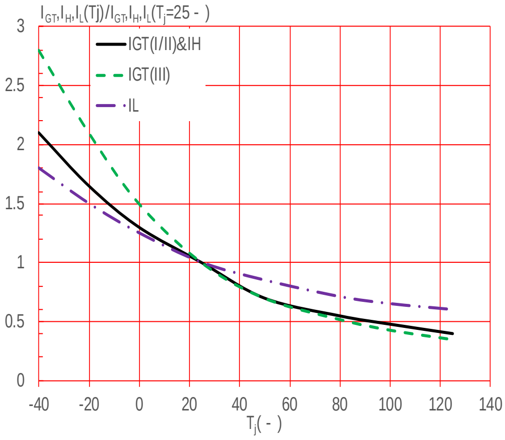
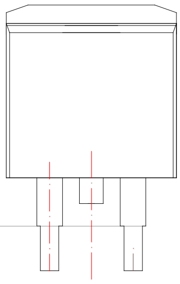


FIG.4: Surge peak on-state current versus number of cycles

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature



PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.40		9.60	0.370		0.378
D	2.40			0.094		
E	1.20		1.50	0.047		0.059
F	0.75		0.85	0.029		0.033

DELIVERY MODE